# Disentanglement of Spin Orbit Torques Originated from Spin Hall Effect and Rashba-Edelstein Effect Using Harmonic Hall Measurements

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#### Abstract

We report on the quantitative separation of the spin orbit torques (SOTs) originated from the spin Hall effect (SHE) and the Rashba-Edelstein effect (REE), by performing the Harmonic Hall measurements for epitaxial platinum/cobalt (Pt/Co) bilayers. The damping-like (DL-) and field-like (FL-)SOT efficiencies ( $\xi_{DL}$  and  $\xi_{FL}$ ) are quantified respectively by fitting the SOT data with corresponding spin-diffusion equation. As a result, the  $\xi_{DL}$ originated from the Pt bulk region ( $\xi_{DL0}$ ) decreases significantly with decreasing temperature, while the  $\xi_{FL}$  from the substrate (sub.)/Pt ( $\xi_{FL1}$ ) and Pt/Co ( $\xi_{FL2}$ ) interface barely change, suggesting that the origin of FL-SOT is the REE instead of the SHE; the sign of  $\xi_{FL1}$  is opposite to  $\xi_{FL2}$ , which is consistent with the REE where the direction of the spin accumulation depends on the interfacial electric field induced by broken inversion symmetry. Moreover, the  $\xi_{DL}$  induced by sub./Pt ( $\xi_{DL1}$ ) and Pt/Co ( $\xi_{DL2}$ ) interfaces are found to be about 1 order of magnitude smaller than maximum  $\xi_{DL0}$ , while their sign are consistent with respective  $\xi_{FL}$  ( $\xi_{FL1}$  and  $\xi_{FL2}$ ). Our work presents a thorough disentanglement of the SOTs in heavy metal/ferromagnet bilayers in which both SHE and REE are present, and provides deterministic answers to the fundamental question on their physical origin.

# 1. Introduction

The recent advances in the spin Hall effect (SHE) have made it possible to manipulate the local magnetizations via electrical means.<sup>1,2</sup> A longitudinal charge current flowing in SH materials such as heavy metals (HMs) generates a transverse pure spin current that exerts a spin orbit torque (SOT) on the neighboring ferromagnetic (FM) layer. Although the origin of the SOT remains controversial, it can be decomposed into two orthogonal components, a (anti-)damping-like (DL) term  $m \times (m \times \sigma)$  and a field-like (FL) term  $m \times \sigma$ , where the m denotes the magnetization of the FM layer, and  $\sigma$  is the spin polarization. Generally, the SHE is considered to be the dominant origin of the DL-SOT,3 and the Rashba-Edelstein effect (REE) is considered to be the main origin of the FL-SOT.<sup>4</sup> However, theoretical studies have shown that the REE can produce a non-trivial DL-SOT,<sup>5–7</sup> e.g. by means of the giant Rashba spin splitting8 at HM/normal metal interfaces; moreover, the SHE can produce a small FL-SOT as well.<sup>7</sup> Therefore, the interface-generated SOT have up to now remained unclear due to the difficulty in the separation of DL-

and FL-SOT because of the presence of both SHE and REE. Here in this work, by performing a detailed harmonic Hall measurement for epitaxial Pt/Co bilayers, we are able to present a thorough, quantitative separation of the SOTs originated from these two effects.

## 2. Experimental methods

Multilayer thin films of  $Pt(t_{Pt})/Co(1.95)/AlO_x(2)$  were sputter-deposited onto  $Al_2O_3(0001)$  and  $Si/SiO_2$  substrates at room temperature (*T*) to make epitaxial (epi-) and polycrystalline (poly-) samples respectively, where the former is the main focus of this study and the latter is the control set. The saturation magnetization ( $M_s$ ) of Co was measured via Vibrating Sample Magnetometer and found to be *T* independent. The harmonic Hall measurements<sup>9,10</sup> were carried out for Hall bar devices that have in-plane magnetic anisotropy.



**Fig. 1** (a) Inverse of the sheet resistance of epi-Pt( $t_{Pt}$ )/Co(1.95)/AlO<sub>x</sub>(2) measured at 10-300 K. Solid lines are linear fitting to the experimental data ranging from 0.2-1.1 nm and 1.3-4.0 nm, respectively. (b) Normalized DL-SOT as a function of  $t_{Pt}$  measured at 10-300 K. Solid lines are fitting to the data (Eq.1) in the range of 1.3-4.0 nm, broken lines are fitting to the data (Eq. 3) in the range of 0.2-1.1 nm. (c) Normalized FL-SOT as a function of  $t_{Pt}$  measured at 10-300 K. Solid lines are fitting to the data (Eq. 2) in the range of 0.2-4.0 nm.



**Fig. 2** (a) Bulk  $\theta_{\text{SH}}$  dependence of FL-SOT efficiency at sub./Pt  $(\xi_{\text{FL1}})$  and Pt/Co  $(\xi_{\text{FL2}})$  interfaces. (b) Bulk  $\theta_{\text{SH}}$  dependence of effective REE thickness at sub./Pt  $(d_{\text{REE1}})$  and Pt/Co  $(d_{\text{REE2}})$  interfaces. (c) REE induced  $\xi_{\text{DL}}$  from sub./Pt  $(\xi_{\text{DL1}})$  and Pt/Co  $(\xi_{\text{DL2}})$  interfaces plotted as a function of respective  $\xi_{\text{FL}}$ .

# 3. Results and discussions

Figure 1(a) shows the inverse sheet resistance as a function of  $t_{\text{Pt}}$ . The data ranging from 0.2-1.1 nm and 1.3-4.0 nm respectively follows a linear relationship, suggesting a constant resistivity in each range. By considering that both SHE and REE contributes to the DL-SOT, the following equation is used to fit the data in Fig. 1(b) with  $t_{\text{Pt}} = 1.3$ -4.0 nm:

 $H_{\rm DL} \approx H_{\rm DL0}(1 - \operatorname{sech}(t_{\rm Pt}/\lambda_{\rm Pt})) + H_{\rm DL2},$  (1) where  $H_{\rm DL0}$  is the DL-SOT induced by bulk Pt,  $\lambda_{\rm Pt}$  is the spin diffusion length (SDL) in Pt, and  $H_{\rm DL2}$  is the DL-SOT generated at Pt/Co interface due to the REE. Note that the effective REE thickness (*e.g.* ~0.4 nm)<sup>11</sup> is estimated to be several times to one order of magnitude smaller compared to such a  $t_{\rm Pt}$  range, therefore it is reasonable to consider  $H_{\rm DL2}$ as a constant for the fitting above.

From the analysis above we obtain the  $H_{\text{DL0}}$  and  $\lambda_{\text{Pt}}$ depending on *T*. The bulk Pt spin Hall angle ( $\theta_{\text{SH}}$ ) (assuming a transparent interface) is calculated via  $\theta_{\text{SH}} =$  $(2eM_{s}t_{\text{F}})/\hbar \times H_{\text{DL0}}/j_c$ , where  $M_s$ ,  $t_{\text{F}}$  and  $j_c$  are saturation magnetization, Co layer thickness and current density in Pt. From the plot of  $\theta_{\text{SH}}-\rho_{\text{Pt}}$  and  $\lambda_{\text{Pt}}-\sigma_{\text{Pt}}$  (not shown due to page limitations) we experimentally obtain an intrinsic and/or sidejump contribution to the SHE and the Elliot-Yafet (EY) spin relaxation in *bulk* Pt, which are consistent with previous study.<sup>12</sup> Qualitatively, the DL- and FL-SOT have shown a significant difference in *T*-dependence (Fig. 1(b) and(c)): the DL-SOT decreases drastically when  $t_{\text{Pt}} \ge 1.3$  nm while the FL-SOT barely changes in all thickness and *T* ranges. Particularly, at  $t_{\text{Pt}} = 6.0$  nm, the FL-SOT remains constant while the DL-SOT decreases by a factor of 3 when *T* drops from 300 K to 10 K. This demonstrates that the FL-SOT efficiency ( $\xi_{\text{FL}}$ ) is independent of the DL-SOT efficiency ( $\xi_{\text{DL}}$ ) via  $\xi_{\text{D(F)L}} = (2eM_s t_{\text{F}})/\hbar \times H_{\text{D(F)L}}/j_c$ . Such a result suggests that the SHE-induced FL-SOT is negligible in our samples.

The  $t_{Pt}$  dependence of  $H_{FL}$  is then quantitatively analyzed and fitted (as shown in Fig. 1(c)) using the equation below based on the spin diffusion model:

$$H_{\rm FL} \approx H_{\rm FL1}(1 - \operatorname{sech}(t_{\rm Pt}/d_{\rm REE1}))\operatorname{sech}(t_{\rm Pt}/\lambda'_{\rm Pt}) + H_{\rm FL2}(1 - \operatorname{sech}(t_{\rm Pt}/d_{\rm REE2})), \qquad (2)$$

where  $H_{\rm FL1}$  and  $H_{\rm FL2}$ ,  $d_{\rm REE1}$  and  $d_{\rm REE2}$  are the FL-SOT, effective REE thickness at sub./Pt and Pt/Co interfaces, respectively. Note that  $\lambda'_{\rm Pt}$ , the SDL with  $t_{\rm Pt} = 0.2$ -1.1 nm, is obtained based on the  $\lambda_{\rm Pt}$ - $\sigma_{\rm Pt}$  plot. The corresponding  $\xi_{\rm FL1}$  and  $\xi_{\rm FL2}$  (Fig. 2(a)) show comparable magnitude but opposite sign, consistent with the REE; the  $d_{\rm REE1}$  and  $d_{\rm REE2}$  (Fig. 2(b)) are quantitatively consistent with previous work.<sup>11</sup>

Finally, the REE induced  $\xi_{DL}$  from sub./Pt ( $\xi_{DL1}$ ) and Pt/Co ( $\xi_{DL2}$ ) interfaces are quantified using the following equation:

 $\begin{aligned} H_{\rm DL} &\approx H_{\rm DL1}(1 - {\rm sech}(t_{\rm Pt}/d_{\rm REE1}))\,{\rm sech}(t_{\rm Pt}/\lambda'_{\rm Pt}) \\ &+ H_{\rm DL2}(1 - {\rm sech}(t_{\rm Pt}/d_{\rm REE2})) \\ &+ H'_{\rm DL0}(1 - {\rm sech}(t_{\rm Pt}/\lambda'_{\rm Pt})), \end{aligned}$ 

where  $H_{\rm DL1}$  and  $H_{\rm DL2}$  are the REE induced DL-SOT from sub./Pt and Pt/Co interfaces.  $H'_{\rm DL0}$  is the SHE induced DL-SOT with  $t_{\rm Pt} = 0.2$ -1.1 nm, estimated based on the  $\theta_{\rm SH}$ - $\rho_{\rm Pt}$ plot. The obtained  $\xi_{\rm DL1}$  and  $\xi_{\rm DL2}$  in Fig. 2(c) show opposite sign, consistent with the sign of  $\xi_{\rm FL1}$  and  $\xi_{\rm FL2}$ .

### 4. Conclusions

We present a thorough, quantitative disentanglement of the SOTs originated from SHE and REE in Pt/Co bilayers. The FL-SOT is found to originate from the REE. The REE induced  $\xi_{FL1}$  and  $\xi_{FL2}$  at sub./Pt, Pt/Co interfaces are of comparable magnitude, but opposite sign, which is consistent with the REE. The REE-induced  $\xi_{DL1}$  and  $\xi_{DL2}$  are also of opposite sign, and are about 1 order of magnitude smaller than the maximum  $\xi_{DL0}$ . This work quantifies the SOT in SH systems with the presence of strong Rashba spin splitting.

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